

# QH8MC5

60V Nch+Pch Power MOSFET

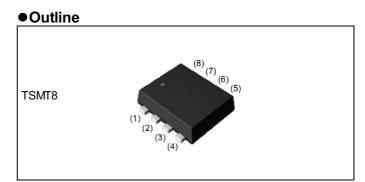
Symbol	Tr1:Nch	Tr2:Pch
V <sub>DSS</sub>	60V	-60V
R <sub>DS(on)</sub> (Max.)	90mΩ	91mΩ
Ι <sub>D</sub>	±3.0A	±3.5A
PD	1.5	5W

## Features

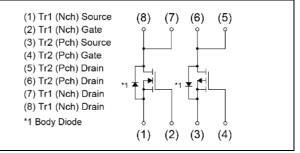
- 1) Low on resistance
- 2) Small Surface Mount Package (TSMT8)
- 3) Pb-free plating ; RoHS compliant
- 4) Halogen Free

Application

Switching



### Inner circuit



## Packaging specifications

	Packing	Embossed Tape
	Reel size (mm)	180
Туре	Tape width (mm)	8
•	Quantity (pcs)	3000
	Taping code	TCR
	Marking	MC5

## • Absolute maximum ratings (T<sub>a</sub> = 25°C ,unless otherwise specified)

Derem	otor	Sumah al	Va	lue	Linit
Param	eter	Symbol	Tr1:Nch	Tr2:Pch	Unit
Drain - Source voltage		V <sub>DSS</sub>	60	-60	V
Continuous drain current		I <sub>D</sub>	±3.0	±3.5	А
Pulsed drain current		I <sub>DP</sub> *1	±12	±14	А
Gate - Source voltage		V <sub>GSS</sub>	±20	±20	V
Avalanche current, single pul	se	I <sub>AS</sub> *2	3.0	-3.5	А
Avalanche energy, single pul	se	E <sub>AS</sub> *2	0.7	1.0	mJ
Dewer dissinction	totol	P <sub>D</sub> *3	1	.5	W
Power dissipation	total	P <sub>D</sub> <sup>*4</sup>	1	.1	vv
Junction temperature		Tj	1	50	°C
Operating junction and storage	ge temperature range	T <sub>stg</sub>	-55 to	+150	°C

### •Thermal resistance

Deventer		Curren ol		Values		Linit
Parameter		Symbol	Min.	Тур.	Max.	Unit
Thermel registered junction embient	total	$R_{thJA}^{*3}$	-	-	83.3	°C/W
Thermal resistance, junction - ambient	total	$R_{thJA}^{*4}$	-	-	113	U/VV

## •Electrical characteristics (T<sub>a</sub> = 25°C)

Deremeter	Cump of	T	Conditions		Values		l Init
Parameter	Symbol	Туре	Conditions	Min.	Тур.	Max.	Unit
Drain - Source breakdown	V	Tr1	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA	60	-	-	V
voltage	V <sub>(BR)DSS</sub>	Tr2	V <sub>GS</sub> = 0V, I <sub>D</sub> = -1mA	-60	-	-	V
Breakdown voltage	ΔV <sub>(BR)DSS</sub>	Tr1	I <sub>D</sub> = 1mA, referenced to 25°C	I	38.9	-	mV/°C
temperature coefficient	$\Delta T_{j}$	Tr2	$I_D = -1 \text{ mA}$ , referenced to 25°C	-	-22	-	mv/ C
Zero gate voltage	1	Tr1	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V	-	-	1	^
drain current	IDSS	Tr2	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V	-	-	-1	μA
Gate - Source	1	Tr1	$V_{GS}$ = ±20V, $V_{DS}$ = 0V	-	-	±100	nA
leakage current	GSS	Tr2	$V_{GS}$ = ±20V, $V_{DS}$ = 0V	-	-	±100	nA
Gate threshold	V	Tr1	$V_{DS} = V_{GS}, I_D = 1mA$	1.0	-	2.5	V
voltage	V <sub>GS(th)</sub>	Tr2	$V_{DS} = V_{GS}, I_D = -1mA$	-1.0	-	-2.5	V
Gate threshold voltage	$\Delta V_{GS(th)}$	Tr1	I <sub>D</sub> = 1mA, referenced to 25°C	-	-4.7	-	m) //ºO
temperature coefficient	$\Delta T_j$	Tr2	$I_D = -1 \text{ mA}$ , referenced to 25°C	-	3.7	-	mV/°C
		Tr1	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.0A	-	70	90	
Static drain - source	<b>D</b> *5	ILL	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.0A	-	100	140	
on - state resistance	R <sub>DS(on)</sub> *5	т-2	V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.5A	-	71	91	mΩ
		Tr2	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.5A	-	79	101	
Cata registance	D	Tr1		-	2.7	-	0
Gate resistance	R <sub>G</sub>	Tr2	-	-	16	-	Ω
Forward Transfer	IV- 1*5	Tr1	V <sub>DS</sub> = 5.0V, I <sub>D</sub> = 3.0A	1.3	-	-	6
Admittance	Y <sub>fs</sub>  * <sup>5</sup>	Tr2	V <sub>DS</sub> = -5V, I <sub>D</sub> = -3.5A	4.0	-	-	S

\*1 Pw  $\leq$  10µs, Duty cycle  $\leq$  1%

\*2 Tr1: L  $\simeq$  0.1mH, V\_{DD} = 30V, R\_G = 25 $\Omega$ , STARTING T\_j = 25°C Fig.3-1,3-2

Tr2: L  $\simeq$  0.1mH, V\_{DD} = -30V, R\_G = 25Ω, STARTING T\_j = 25°C Fig.6-1,6-2

\*3 Mounted on a ceramic board (30×30×0.8mm)

\*4 Mounted on a FR4 (25×25×0.8mm)

\*5 Pulsed



## Datasheet

## • Electrical characteristics (T<sub>a</sub> = 25°C)

<Tr1>

Deremeter	Cump of	Conditions		Values		Lincit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	135	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 30V	-	38	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	6	-	
Turn - on delay time	t <sub>d(on)</sub> *5	$V_{DD} \simeq 30V$ , $V_{GS}$ = 10V	-	5.3	-	
Rise time	t <sub>r</sub> *5	I <sub>D</sub> = 1.5A	-	4.8	-	20
Turn - off delay time	$t_{d(off)}$ *5	R <sub>L</sub> = 20Ω	-	13.0	-	ns
Fall time	t <sub>f</sub> *5	R <sub>G</sub> = 10Ω	-	3.1	-	

### <Tr2>

Deremeter	Sumbol	Conditions	,	Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	850	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -30V	-	60	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	40	-	
Turn - on delay time	$t_{d(on)}$ *5	$V_{DD} \simeq$ -30V, $V_{GS}$ = -10V	-	9.2	-	
Rise time	t <sub>r</sub> *5	I <sub>D</sub> = -1.75A	-	10.0	-	20
Turn - off delay time	$t_{d(off)}$ *5	R <sub>L</sub> = 17.1Ω	-	82.0	-	ns
Fall time	t <sub>f</sub> *5	R <sub>G</sub> = 10Ω	-	43.0	-	



## • Gate charge characteristics ( $T_a = 25^{\circ}C$ )

<Tr1>

Deremeter	Sumbol	Symbol Conditions		Values			Unit
Parameter	Symbol	Conai	lions	Min.	Тур.	Max.	Unit
Total gata abarga	O *5		V <sub>GS</sub> = 10V	-	3.1	-	
Total gate charge	$Q_g^{*5}$	$V_{DD} \simeq 30V$		-	1.7	-	
Gate - Source charge	Q <sub>gs</sub> *5	I <sub>D</sub> = 3.0A	V <sub>GS</sub> = 4.5V	-	0.9	-	nC
Gate - Drain charge	$Q_{gd}^{*5}$			-	0.3	-	

### <Tr2>

Deremeter	Sumbol	bol Conditions -			Values		
Parameter	Symbol	Conai	uons	Min.	Тур.	Max.	Unit
Total acta charge	O *5		V <sub>GS</sub> = -10V	-	17.3	-	
Total gate charge	$Q_g^{*5}$	V <sub>DD</sub> ≃ -30V		-	8.5	-	nC
Gate - Source charge	Q <sub>gs</sub> *5	I <sub>D</sub> = -3.5A	V <sub>GS</sub> = -4.5V	-	2.6	-	nc
Gate - Drain charge	$Q_{gd}^{*5}$			-	3.4	-	

## •Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

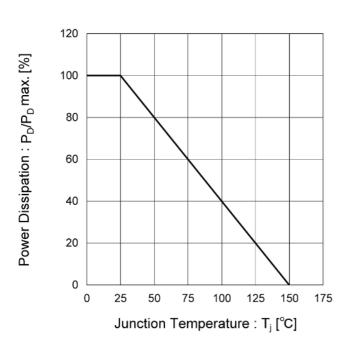
<Tr1>

Deremeter	C) mah al	Conditions		Values		Linit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Continuous forward current	I <sub>S</sub>	T <sub>a</sub> = 25°C	-	-	1.25	^
Pulse forward current	I <sub>SP</sub> *1	$T_a = 250$	-	-	12	A
Forward voltage	V <sub>SD</sub> *5	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.25A	-	-	1.2	V
Reverse recovery time	t <sub>rr</sub> *5	I <sub>S</sub> = 3.0A, V <sub>GS</sub> = 0V	-	23	-	ns
Reverse recovery charge	Q <sub>rr</sub> *5	di/dt = 100A/µs	-	20	-	nC

<Tr2>

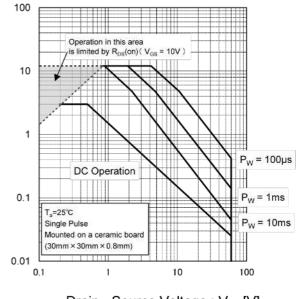
Parameter	Symbol Conditions		Values			Unit
	Symbol	Conditions	Min.	Тур.	Max.	Unit
Continuous forward current	ا <sub>s</sub>	T <sub>a</sub> = 25°C	-	-	-1.25	^
Pulse forward current	I <sub>SP</sub> *1	$T_a = 25 C$	-	-	-14	A
Forward voltage	$V_{SD}^{*5}$	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.25A	-	-	-1.2	V
Reverse recovery time	t <sub>rr</sub> *5	I <sub>S</sub> = -3.5A, V <sub>GS</sub> = 0V	-	25	-	ns
Reverse recovery charge	Q <sub>rr</sub> *5	di/dt = 100A/µs	-	23	-	nC





## Fig.1 Power Dissipation Derating Curve

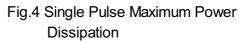
Fig.2 Maximum Safe Operating Area

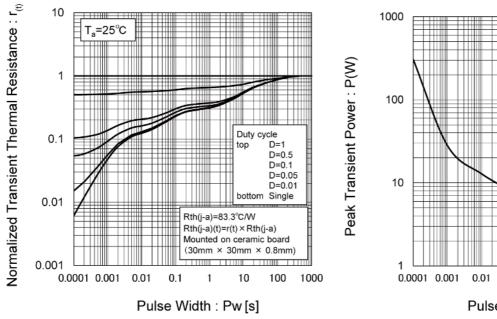


Drain Current : I<sub>D</sub> [A]

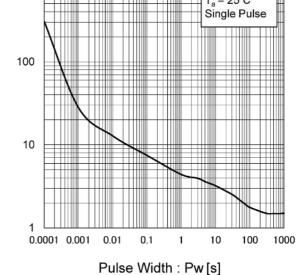
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

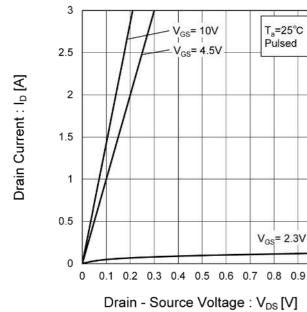




0  $T_a = 25^{\circ}C$ 







## Fig.5 Typical Output Characteristics(I)

T<sub>a</sub>=25°C

Pulsed

V<sub>GS</sub>= 2.3V

1

Fig.6 Typical Output Characteristics(II)

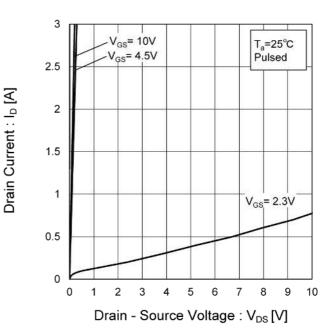
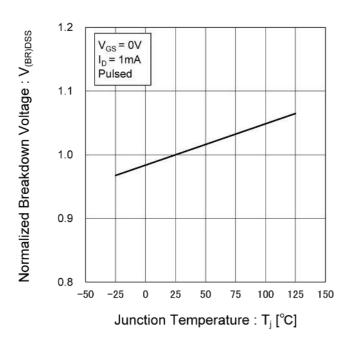
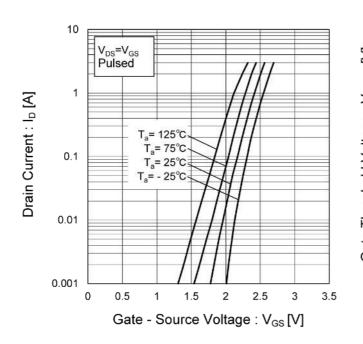


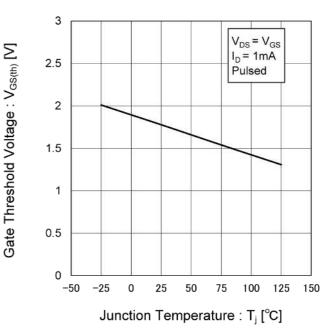
Fig.7 Breakdown Voltage vs. **Junction Temperature** 





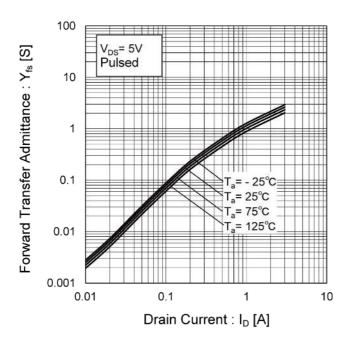


## Fig.8 Typical Transfer Characteristics



### Fig.9 Gate Threshold Voltage vs. Junction Temperature

## Fig.10 Forward Transfer Admittance vs. Drain Current





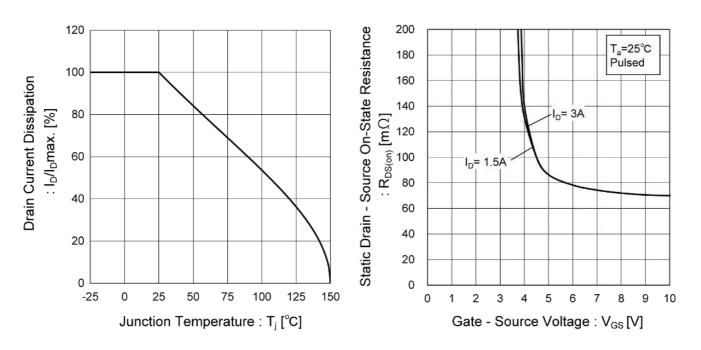
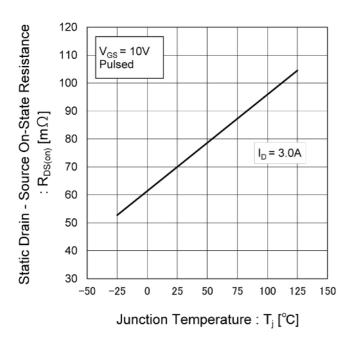


Fig.11 Drain Current Derating Curve

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature





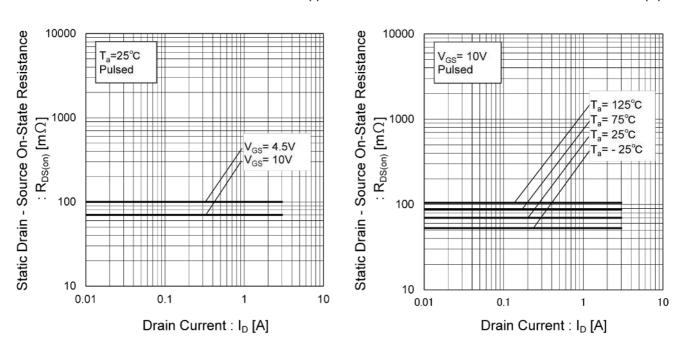


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current (I) Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (II)

Fig.16 Static Drain - Source On - State Resistance vs. Drain Current (III)

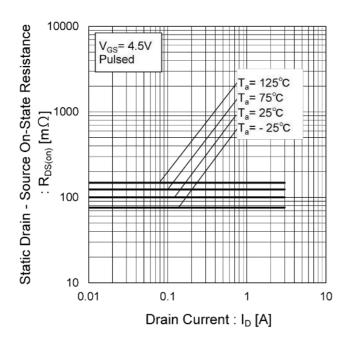
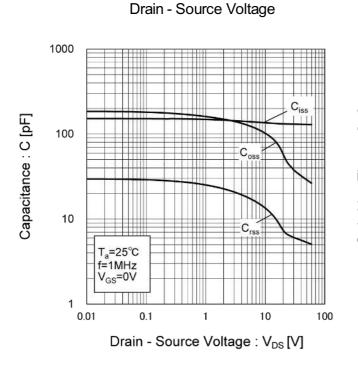




Fig.17 Typical Capacitances vs.



### Fig.18 Switching Characteristics

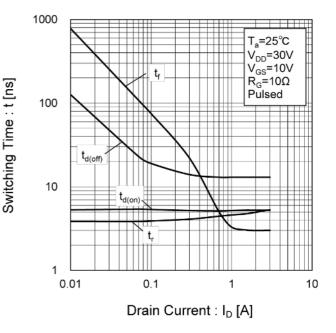


Fig.19 Typical Gate Charge

Gate - Source Voltage : V<sub>GS</sub> [V]

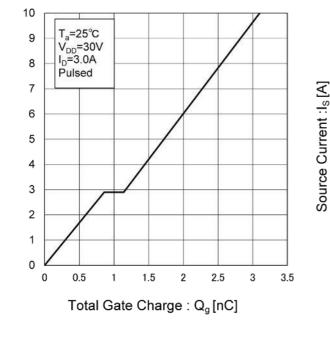
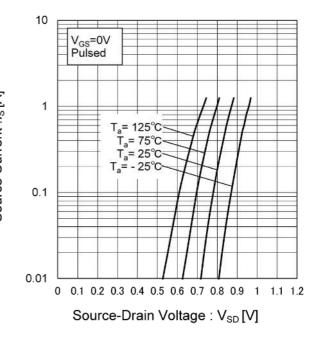
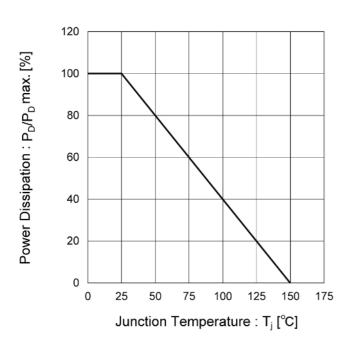


Fig.20 Source Current vs. Source Drain Voltage



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## Fig.1 Power Dissipation Derating Curve

Fig.2 Maximum Safe Operating Area

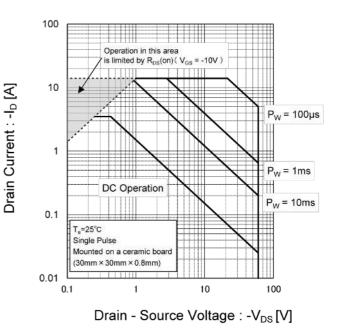
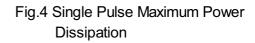
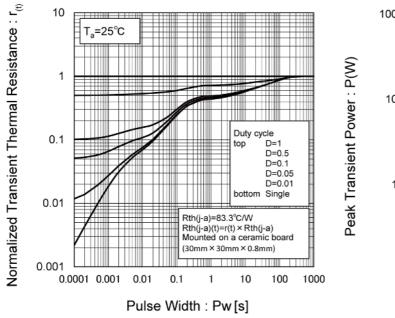
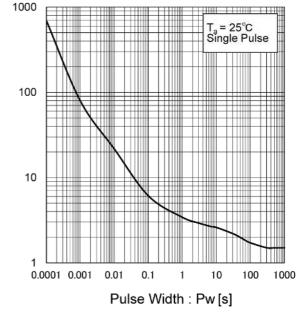


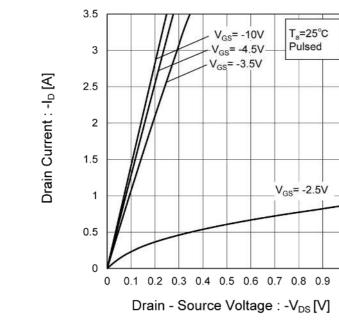
Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width







ROHM



## Fig.5 Typical Output Characteristics(I)

Fig.6 Typical Output Characteristics(II)

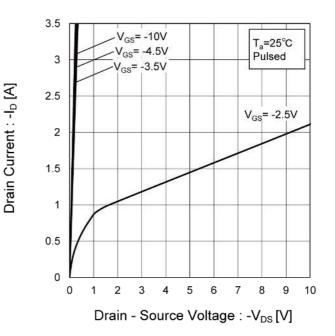
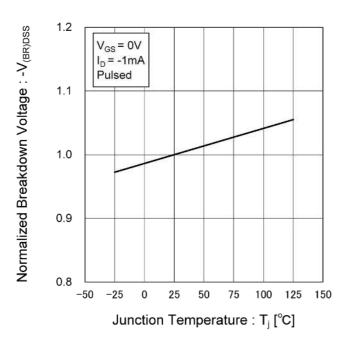
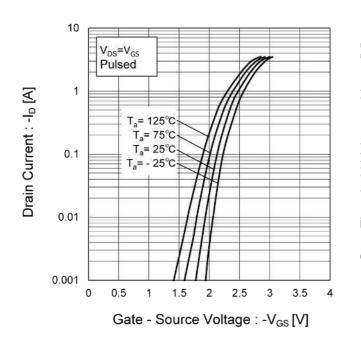


Fig.7 Breakdown Voltage vs. Junction Temperature



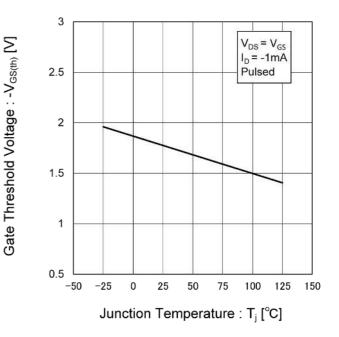
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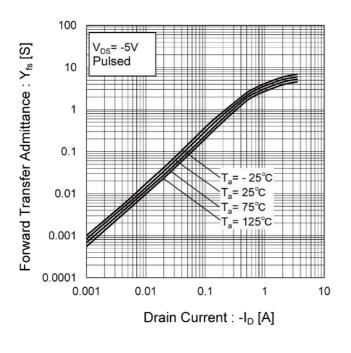


## Fig.8 Typical Transfer Characteristics

Fig.9 Gate Threshold Voltage vs. Junction Temperature



## Fig.10 Forward Transfer Admittance vs. Drain Current





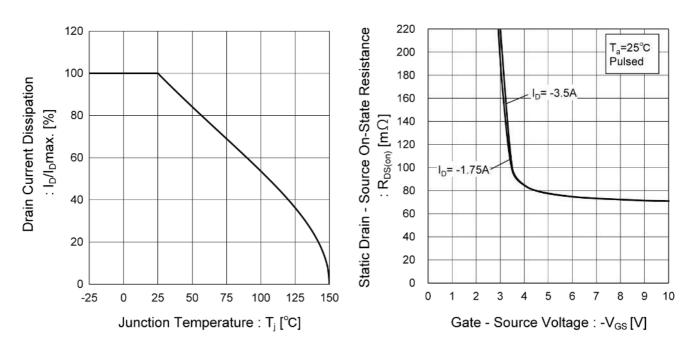
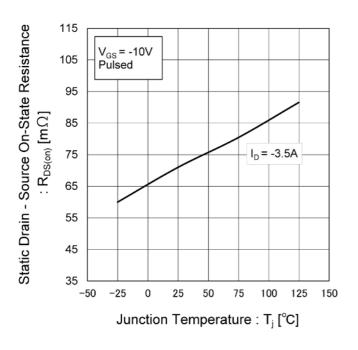


Fig.11 Drain Current Derating Curve

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature





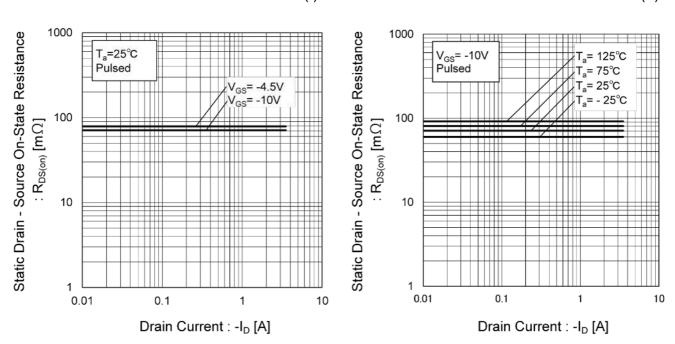


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current (I) Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (II)

Fig.16 Static Drain - Source On - State Resistance vs. Drain Current (III)

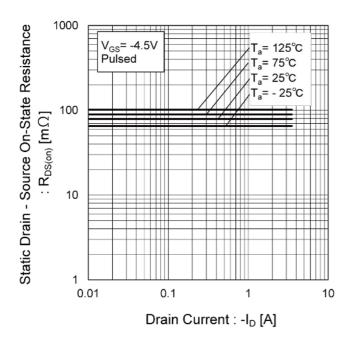
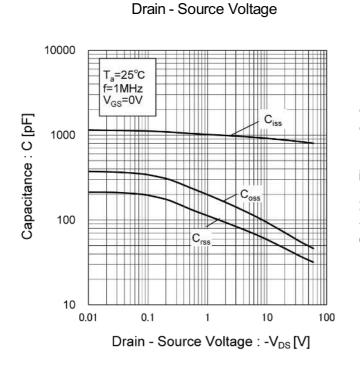




Fig.17 Typical Capacitances vs.



## Fig.18 Switching Characteristics

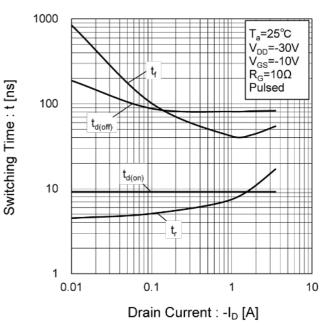


Fig.19 Typical Gate Charge

Gate - Source Voltage : -V<sub>GS</sub> [V]

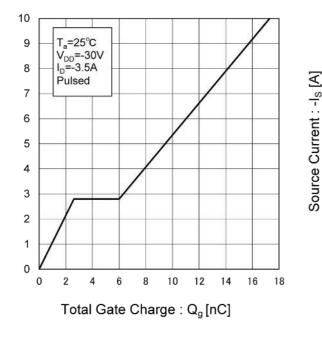
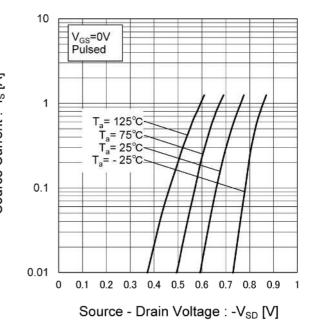


Fig.20 Source Current vs. Source Drain Voltage



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## Measurement circuits <Tr1>

Fig.1-1 Switching Time Measurement Circuit

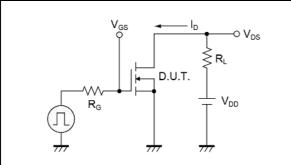


Fig.2-1 Gate Charge Measurement Circuit

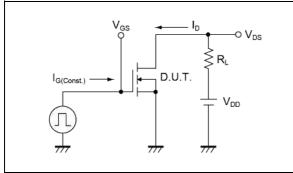


Fig.3-1 Avalanche Measurement Circuit

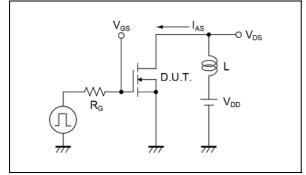
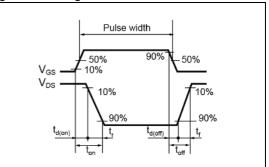
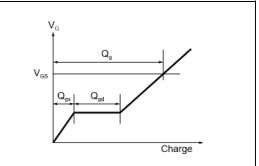


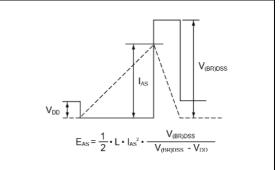
Fig.1-2 Switching Waveforms



### Fig.2-2 Gate Charge Waveform



### Fig.3-2 Avalanche Waveform





## Measurement circuits <Tr2>

Fig.4-1 Switching Time Measurement Circuit

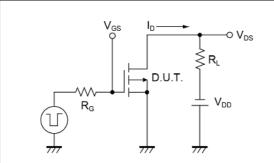


Fig.5-1 Gate Charge Measurement Circuit

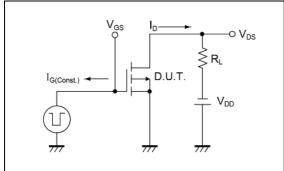


Fig.6-1 Avalanche Measurement Circuit

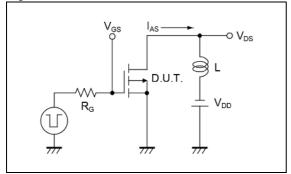
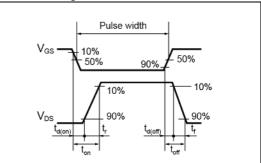
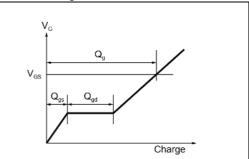


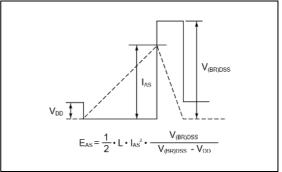
Fig.4-2 Switching Waveforms







### Fig.6-2 Avalanche Waveform



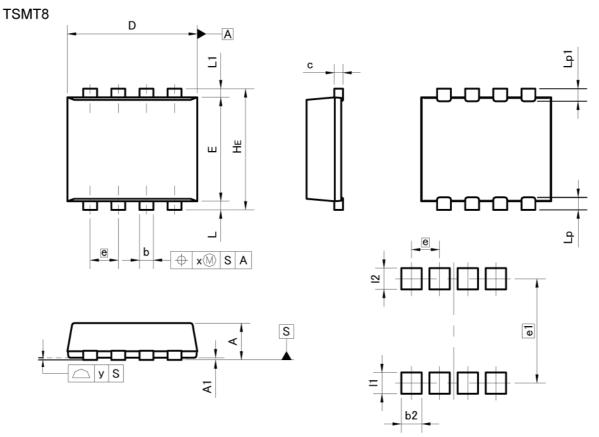
## Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.





## Dimensions



Pattern of terminal position areas [Not a pattern of soldering pads]

DIM	MILIM	ETERS	INC	HES
	MIN	MAX	MIN	MAX
A	0.75	0.85	0.030	0.033
A1	0.00	0.05	0.000	0.002
b	0.27	0.37	0.011	0.015
с	0.12	0.22	0.005	0.009
D	2.90	3.10	0.114	0.122
E	2.30	2.50	0.091	0.098
е	0.	65	0.0	26
HE	2.70	2.90	0.106	0.114
L	0.10	0.30	0.004	0.012
L1	0.10	0.30	0.004	0.012
Lp	0.19	0.39	0.007	0.015
Lp1	0.19	0.39	0.007	0.015
x	875	0.10	1	0.004
v	0	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.47	-	0.019
e1	2.41		0.095	
11	-	0.49	-	0.019
12	2 <del></del>	0.49	3.00	0.019

Dimension in mm/inches

ROHM

# Notice

#### Precaution on using ROHM Products

1. Our Products are designed and manufactured for application in ordinary electronic equipment (such as AV equipment, OA equipment, telecommunication equipment, home electronic appliances, amusement equipment, etc.). If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (<sup>Note 1)</sup>, transport equipment, traffic equipment, aircraft/spacecraft, nuclear power controllers, fuel controllers, car equipment including car accessories, safety devices, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the S	pecific Applications
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JAPAN	USA	EU	CHINA
CLASSⅢ	CLASSⅢ	CLASS II b	CLASSII
CLASSⅣ	CLASSIII	CLASSⅢ	CLASSI

- 2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
  - [a] Installation of protection circuits or other protective devices to improve system safety
  - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
- 3. Our Products are designed and manufactured for use under standard conditions and not under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc, prior to use, must be necessary:
  - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

### Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

#### **Precaution for Product Label**

A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

#### Precaution for Disposition

When disposing Products please dispose them properly using an authorized industry waste company.

#### Precaution for Foreign Exchange and Foreign Trade act

Since concerned goods might be fallen under listed items of export control prescribed by Foreign exchange and Foreign trade act, please consult with ROHM in case of export.

#### **Precaution Regarding Intellectual Property Rights**

- 1. All information and data including but not limited to application example contained in this document is for reference only. ROHM does not warrant that foregoing information or data will not infringe any intellectual property rights or any other rights of any third party regarding such information or data.
- 2. ROHM shall not have any obligations where the claims, actions or demands arising from the combination of the Products with other articles such as components, circuits, systems or external equipment (including software).
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#### **Other Precaution**

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- 4. The proper names of companies or products described in this document are trademarks or registered trademarks of ROHM, its affiliated companies or third parties.

### **General Precaution**

- 1. Before you use our Products, you are requested to care fully read this document and fully understand its contents. ROHM shall not be in an y way responsible or liable for failure, malfunction or accident arising from the use of a ny ROHM's Products against warning, caution or note contained in this document.
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- 3. The information contained in this document is provided on an "as is" basis and ROHM does not warrant that all information contained in this document is accurate an d/or error-free. ROHM shall not be in an y way responsible or liable for any damages, expenses or losses incurred by you or third parties resulting from inaccuracy or errors of or concerning such information.